

THE SPECIFICATION OF AlGaAs PR LED CHIP “YL-C670nM-F6A”

1. DESCRIPTION

This is a AlGaAs red LED chip. It is N-side up. The peak wavelength is 670 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25°C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V_F) IF=7.2mA		1.70		V
Reverse Voltage (V_R) IR=10 μ A	4			V
or Reverse Current (I_R) Vr=4V			10	(μ A)
Radiated Power ¹⁾ (P_o) IF=6.3mA	0.07			mW
Peak Wavelength (λ_p) IF=5mA	655	670	685	nm
Spectral Radiation Bandwidth ($\Delta \lambda$) IF=5mA		20		nm
Rise Time (T_r) IFp=6.3mA Tw=125ns,Duty=50%		20		ns
Fall Time (T_f) IFp=6.3mA Tw=125ns,Duty=50%		20		ns

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current	: 20 mA(DC)
Reverse Voltage	: 4 V(IR=10 μ A)
Storage Temperature	
while on mylar membrane	: 0 to 40 °C
after removal from mylar membrane	: -40 to 100 °C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1) Material	: AlGaAs
2) Structure	: Double Hetero Structure
3) Junction Size	: 0.280mm \times 0.280mm
4) Thickness	: 0.280mm
5) Bond Pad Size	: 0.140mm diameter
6) Anode Metallization	: Gold Alloy
7) Cathode Metallization	: Gold Alloy

5. Physical Dimensions

Model YL-C670nM-F6A

